



Ruttonsha International Rectifier Ltd.

SILICON RECTIFIERS

TYPE: R600E...F SERIES

FAST RECOVERY DIODES

Hockey Puk Version4

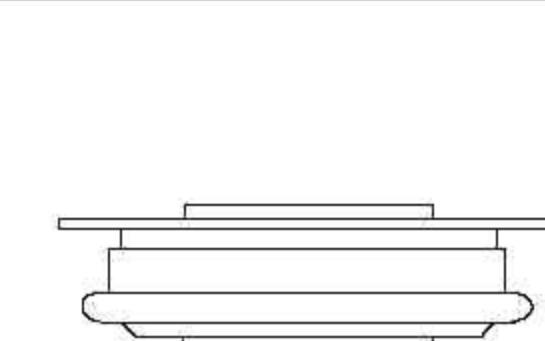
Features

- High power FAST recovery diode series
- High voltage ratings up to 2200V
- High current capability
- Optimized turn on and turn off characteristics
- Low forward recovery
- Fast and soft reverse recovery
- Press-puk encapsulation
- Case style conform to JEDEC B-43
- Maximum junction temperature 125°C

600A

Typical Applications

- Snubber diode for GTO
- High voltage free-wheeling diode
- Fast recovery rectifier applications



case style B-43

Major Ratings and Characteristics

Parameters	R600E...F	Units
$I_{F(AV)}$	600	A
@ T_{hs}	55	°C
$I_{F(RMS)}$	942	A
@ T_{hs}	55	°C
I_{FSM}	8320	A
I^2t	346	KA ² s
V_{RRM} range	400 to 2200	V
t_{rr} range	3.2	μs
@ T_J	25	°C
T_J	- 40 to 125	°C

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ELECTRICAL SPECIFICATIONS

Voltage Ratings

Type number	Voltage Code	V_{RRM} max. repetitive peak and off-state voltage V	V_{RSM} , maximum non-repetitive peak voltage V	I_{RRM} max. $T_J = 125^\circ C$ mA
R600E...10CF	04	400	500	45
	08	800	900	
	10	1000	1100	
R600E...16CF	12	1200	1300	45
	14	1400	1500	
	16	1600	1700	
R600E...22CF	20	2000	2100	45
	22	2200	2300	

Forward Conduction

Parameter	R600E...F	Units	Conditions
$I_{F(AV)}$ Max. average forward current @ Heatsink temperature	600	A	180° conduction, half sine wave.
	55	°C	Double side cooled
$I_{F(RMS)}$ Max. RMS current	942	A	@ 55 °C heatsink temperature double side cooled
I_{FSM} Max. peak, one-cycle non-repetitive forward current	8320	A	t = 10ms
			Sinusoidal half wave, Initial $T_J = T_J$ max.
I^2t Maximum I^2t for fusing	346	KA ² s	t = 10ms
$I^2\sqrt{t}$ Maximum $I^2\sqrt{t}$ for fusing	3460	KA ² \sqrt{s}	t = 0.1 to 10ms, no voltage reapplied
$V_{F(TO)}$ Threshold voltage	1.36	V	$T_J = T_J$ max.
r_{f1} Forward slope resistance	0.70	mΩ	$T_J = T_J$ max.
V_{FM} Max. forward voltage	2.97	V	$I_{pk}=1885 A, T_J = 25^\circ C, t_p = 10ms$ sinusoidal wave
trr Reverse Recovery Time	3.2	us	IFM=1000 A, di/dt=25A/us

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Thermal and Mechanical Specifications

Parameter	R600E...F	Units	Conditions
T_J	Max. operating temperature range	-40 to 125	
T_{stg}	Max. storage temperature range	-40 to 150	°C
R_{thJ-hs}	Max. thermal resistance, junction to heatsink	0.050	K/W DC operation double side cooled
F	Mounting force, ± 10%	9800 (1000)	N (Kg)
wt	Approximate weight	83	g
Case style	B-43		See Outline Table

Ordering Information Table

Device Code		R	600	E	22	C	F
1	- R = Diode	1	2	3	4	5	6
2	- Essential part number						
3	- E = Puk Case B-43						
4	- Voltage code: Code x 100 = V_{RRM} (see Voltage Ratings table)						
5	- C = Ceramic Puk						
6	- F = Fast recovery						

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Outline Table

